

SILICON PNP POWER DARLINGTON TRANSISTOR

- SGS-THOMSON PREFERRED SALESTYPE
- PNP DARLINGTON
- HIGH GAIN
- HIGH CURRENT
- HIGH DISSIPATION
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE

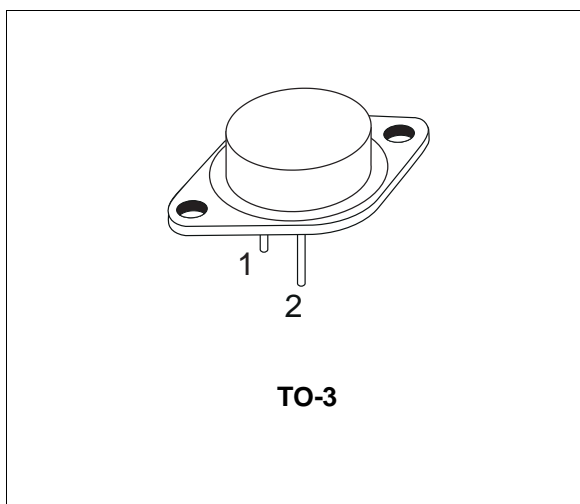
APPLICATIONS

- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

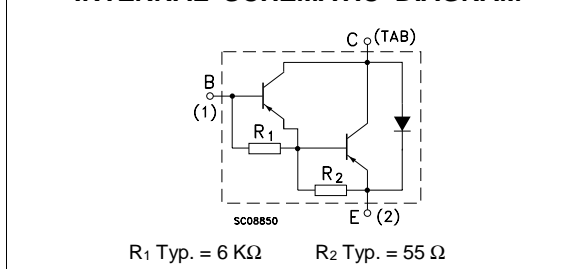
DESCRIPTION

The 2N6050 is a silicon epitaxial-base PNP transistors in monolithic Darlington configuration mounted in Jedec TO-3 metal case.

It is intended for use in power linear and low frequency switching applications.



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage (I _E = 0)	-60	V
V _{CEX}	Collector-Emitter Voltage (V _{BE} = -1.5V)	-60	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	-60	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	-5	V
I _C	Collector Current	-12	A
I _{CM}	Collector Peak Current	-20	A
I _B	Base Current	-0.2	A
P _{tot}	Total Dissipation at T _c ≤ 25 °C	150	W
T _{stg}	Storage Temperature	-65 to 200	°C
T _j	Max. Operating Junction Temperature	200	°C

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	3.12	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	83.3	°C/W

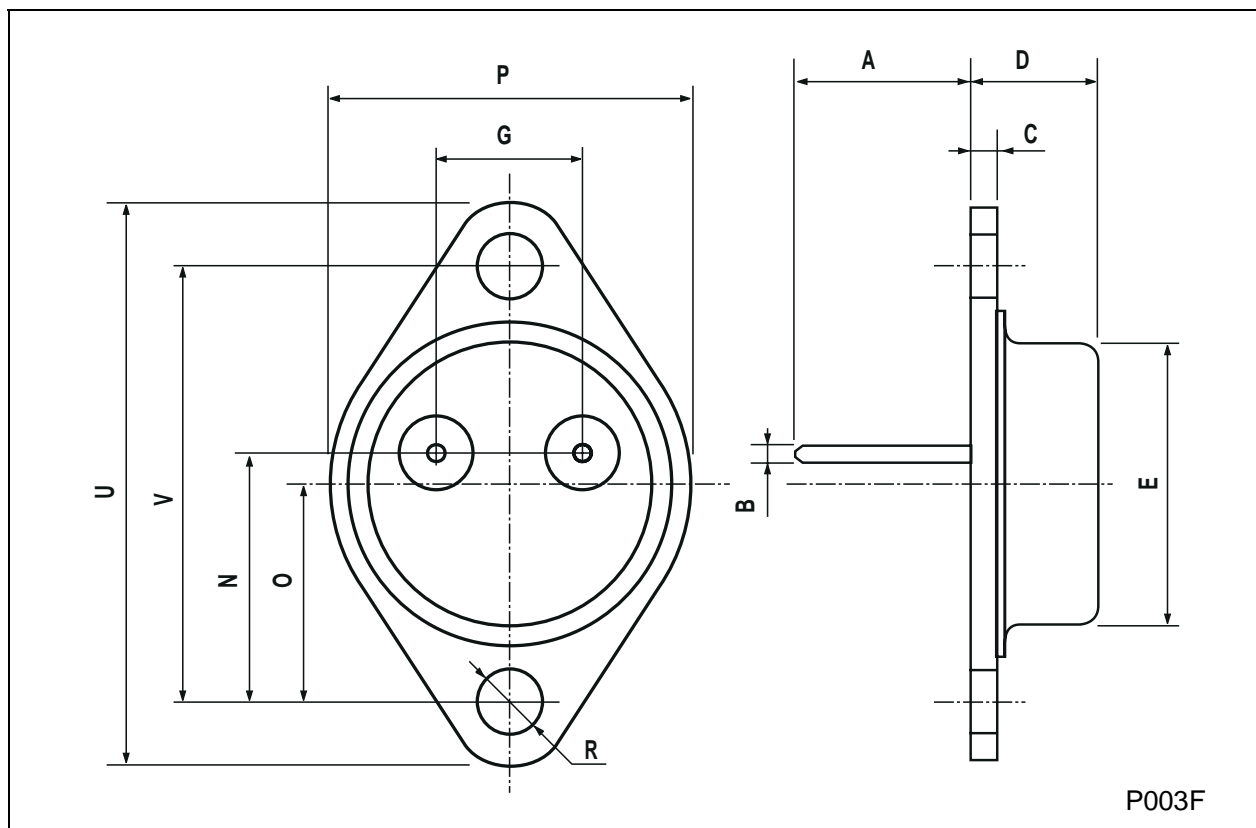
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{C EX}	Collector Cut-off Current (V _{BE} = -1.5V)	V _{CE} = rated V _{CEO} V _{CE} = rated V _{CEO} T _c = 125 °C			0.1 0.5	mA mA
I _{C BO}	Collector Cut-off Current (I _E = 0)	V _{CE} = rated V _{CBO}			0.1	mA
I _{C EO}	Collector Cut-off Current (I _B = 0)	V _{CE} = rated V _{CEO}			0.1	mA
I _{E BO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			2	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage	I _C = 100 mA	80			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 2 A I _B = 8 mA I _C = 4 A I _B = 40 mA			2 3	V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = 4 A I _B = 40 mA			4	V
V _{BE*}	Base-Emitter Voltage	I _C = 2 A V _{CE} = 3 V			2.8	V
h _{FE*}	DC Current Gain	I _C = 0.5 A V _{CE} = 3 V I _C = 2 A V _{CE} = 3 V I _C = 4 A V _{CE} = 3 V	500 750 100		15000	
h _{fe}	Small Signal Current Gain	I _C = 0.75 A V _{CE} = 10 V f = 1KHz	25			
C _{CBO}	Collector Base Capacitance	I _E = 0 V _{CB} = 10 V f = 1MHz for NPN types for PNP types			100 200	pF pF

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

TO-3 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00		13.10	0.433		0.516
B	0.97		1.15	0.038		0.045
C	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
P	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



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